

MC14585B

4-Bit Magnitude Comparator

The MC14585B 4-Bit Magnitude Comparator is constructed with complementary MOS (CMOS) enhancement mode devices. The circuit has eight comparing inputs (A3, B3, A2, B2, A1, B1, A0, B0), three cascading inputs (A < B, A = B, and A > B), and three outputs (A < B, A = B, and A > B). This device compares two 4-bit words (A and B) and determines whether they are “less than”, “equal to”, or “greater than” by a high level on the appropriate output. For words greater than 4-bits, units can be cascaded by connecting outputs (A > B), (A < B), and (A = B) to the corresponding inputs of the next significant comparator. Inputs (A < B), (A = B), and (A > B) on the least significant (first) comparator are connected to a low, a high, and a low, respectively.

Applications include logic in CPU's, correction and/or detection of instrumentation conditions, comparator in testers, converters, and controls.

Features

- Diode Protection on All Inputs
- Expandable
- Applicable to Binary or 8421-BCD Code
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load over the Rated Temperature Range
- Can be Cascaded – See Figure 3
- Pb-Free Packages are Available*

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Parameter	Symbol	Value	Unit
DC Supply Voltage Range	V _{DD}	-0.5 to +18.0	V
Input or Output Voltage Range (DC or Transient)	V _{in} , V _{out}	-0.5 to V _{DD} + 0.5	V
Input or Output Current (DC or Transient) per Pin	I _{in} , I _{out}	±10	mA
Power Dissipation per Package (Note 1)	P _D	500	mW
Ambient Temperature Range	T _A	-55 to +125	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Lead Temperature (8-Second Soldering)	T _L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Temperature Derating: Plastic “P and D/DW”
Packages: - 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range V_{SS} ≤ (V_{in} or V_{out}) ≤ V_{DD}.

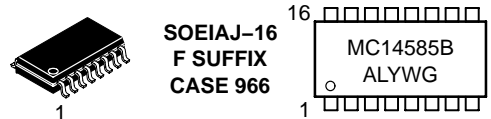
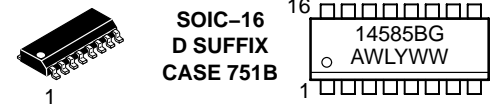
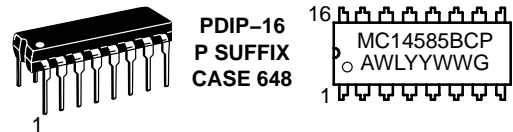
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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MARKING DIAGRAMS



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
MC14585BCP	PDIP-16	25 Units / Rail
MC14585BCPG	PDIP-16 (Pb-Free)	25 Units / Rail
MC14585BD	SOIC-16	48 Units / Rail
MC14585BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14585BDR2	SOIC-16	2500/Tape & Reel
MC14585BDR2G	SOIC-16 (Pb-Free)	2500/Tape & Reel
MC14585BFEL	SOEIAJ-16	2000/Tape & Reel
MC14585BFELG	SOEIAJ-16 (Pb-Free)	2000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V _{DD} Vdc	- 55° C		25° C			125° C		Unit
			Min	Max	Min	Typ (Note 2)	Max	Min	Max	
Output Voltage V _{in} = V _{DD} or 0 V _{in} = 0 or V _{DD}	"0" Level V _{OL}	5.0	-	0.05	-	0	0.05	-	0.05	Vdc
		10	-	0.05	-	0	0.05	-	0.05	
		15	-	0.05	-	0	0.05	-	0.05	
	"1" Level V _{OH}	5.0	4.95	-	4.95	5.0	-	4.95	-	Vdc
		10	9.95	-	9.95	10	-	9.95	-	
		15	14.95	-	14.95	15	-	14.95	-	
Input Voltage (V _O = 4.5 or 0.5 Vdc) (V _O = 9.0 or 1.0 Vdc) (V _O = 13.5 or 1.5 Vdc) (V _O = 0.5 or 4.5 Vdc) (V _O = 1.0 or 9.0 Vdc) (V _O = 1.5 or 13.5 Vdc)	"0" Level V _{IL}	5.0	-	1.5	-	2.25	1.5	-	1.5	Vdc
		10	-	3.0	-	4.50	3.0	-	3.0	
		15	-	4.0	-	6.75	4.0	-	4.0	
	"1" Level V _{IH}	5.0	3.5	-	3.5	2.75	-	3.5	-	Vdc
		10	7.0	-	7.0	5.50	-	7.0	-	
		15	11	-	11	8.25	-	11	-	
Output Drive Current (V _{OH} = 2.5 Vdc) (V _{OH} = 4.6 Vdc) (V _{OH} = 9.5 Vdc) (V _{OH} = 13.5 Vdc) (V _{OL} = 0.4 Vdc) (V _{OL} = 0.5 Vdc) (V _{OL} = 1.5 Vdc)	Source I _{OH}	5.0	-3.0	-	-2.4	-4.2	-	-1.7	-	mAdc
		5.0	-0.64	-	-0.51	-0.88	-	-0.36	-	
		10	-1.6	-	-1.3	-2.25	-	-0.9	-	
	Sink I _{OL}	5.0	0.64	-	0.51	0.88	-	0.36	-	mAdc
		10	1.6	-	1.3	2.25	-	0.9	-	
		15	4.2	-	3.4	8.8	-	2.4	-	
Input Current	I _{in}	15	-	±0.1	-	±0.00001	±0.1	-	±1.0	μAdc
Input Capacitance (V _{in} = 0)	C _{in}	-	-	-	-	5.0	7.5	-	-	pF
Quiescent Current (Per Package)	I _{DD}	5.0	-	5.0	-	0.005	5.0	-	150	μAdc
		10	-	10	-	0.010	10	-	300	
		15	-	20	-	0.015	20	-	600	
Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Package) (C _L = 50 pF on all outputs, all buffers switching)	I _T	5.0	I _T = (0.6 μA/kHz) f + I _{DD}							μAdc
		10	I _T = (1.2 μA/kHz) f + I _{DD}							
		15	I _T = (1.8 μA/kHz) f + I _{DD}							

- Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
- The formulas given are for the typical characteristics only at 25°C.
- To calculate total supply current at loads other than 50 pF: I_T(C_L) = I_T(50 pF) + (C_L - 50) Vfk where: I_T is in μA (per package), C_L in pF, V = (V_{DD} - V_{SS}) in volts, f in kHz is input frequency, and k = 0.001.

SWITCHING CHARACTERISTICS (Note 5) (C_L = 50 pF, T_A = 25°C)

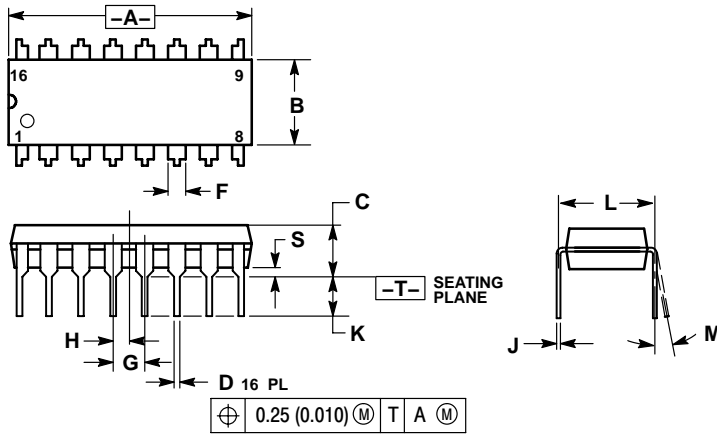
Characteristic	Symbol	V _{DD}	Min	Typ (Note 6)	Max	Unit
Output Rise and Fall Time t _{TLH} , t _{THL} = (1.5 ns/pF) C _L + 25 ns t _{TLH} , t _{THL} = (0.75 ns/pF) C _L + 12.5 ns t _{TLH} , t _{THL} = (0.55 ns/pF) C _L + 9.5 ns	t _{TLH} , t _{THL}	5.0	-	100	200	ns
		10	-	50	100	
		15	-	40	80	
Turn-On, Turn-Off Delay Time t _{PLH} , t _{PHL} = (1.7 ns/pF) C _L + 345 ns t _{PLH} , t _{PHL} = (0.66 ns/pF) C _L + 147 ns t _{PLH} , t _{PHL} = (0.5 ns/pF) C _L + 105 ns	t _{PLH} , t _{PHL}	5.0	-	430	860	ns
		10	-	180	360	
		15	-	130	260	

- The formulas given are for the typical characteristics only at 25°C.
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PACKAGE DIMENSIONS

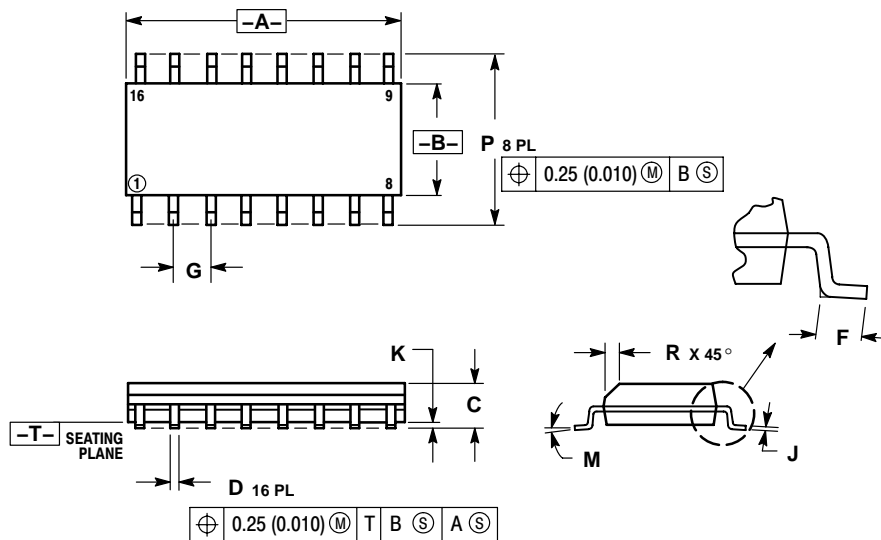
PDIP-16
CASE 648-08
ISSUE T



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01

SOIC-16
CASE 751B-05
ISSUE J



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019